

PSMN009-100P

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 4 — 27 December 2011

Product data sheet

1. Product profile

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- High frequency computer motherboard DC-to-DC convertors
- OR-ing applicationss

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V		
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	75	Α		
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	230	W		
Static char	racteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	7.5	8.8	mΩ		
Dynamic o	Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ Compart 1}}$	-	44	-	nC		



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow A$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN009-100P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 {}^{\circ}\text{C}; T_j \ge 25 {}^{\circ}\text{C}; R_{GS} = 20 {}^{k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	65	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{see } \frac{\text{Figure 3}}{\text{Figure 3}}};$	-	75	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	400	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	230	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V_{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \text{ μs}$; $T_j \le 150 \text{ °C}$; $\delta = 25 \text{ %}$	-30	30	V
Source-dra	in diode				
Is	source current	T _{mb} = 25 °C	-	75	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$	-	400	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 35 A; V_{sup} = 15 V; unclamped; t_p = 0.1 ms; R_{GS} = 50 Ω	-	120	mJ
I _{DS(AL)S}	non-repetitive drain-source avalanche current	V_{GS} = 10 V; V_{sup} = 15 V; R_{GS} = 50 Ω ; $T_{j(init)}$ = 25 °C; unclamped	-	75	Α

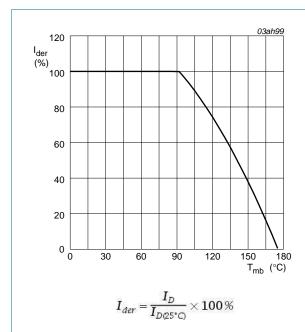


Fig 1. Normalized continuous drain current as a function of mounting base temperature

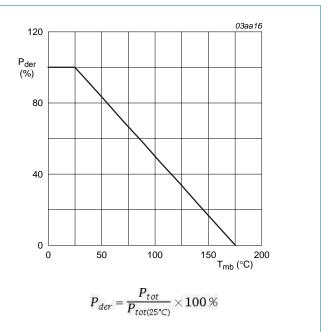
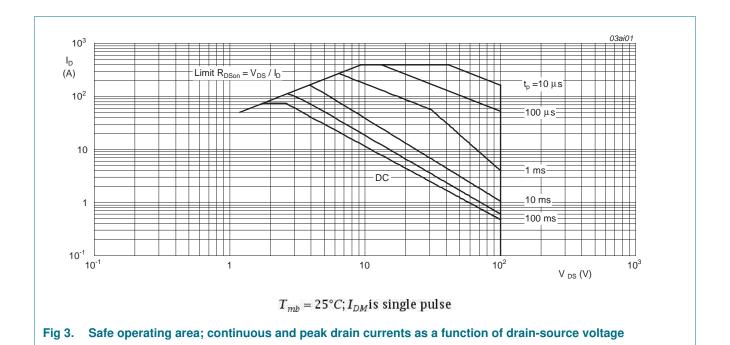


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

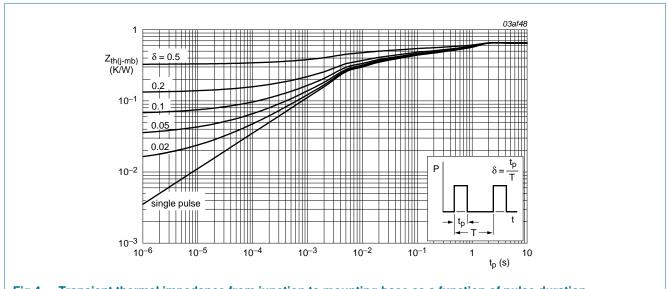


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 8	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 8	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 8	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS} gate leakage current	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nΑ
R _{DSon} drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 9; see Figure 10	-	20.25	23.8	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 9; see Figure 10	-	7.5	8.8	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	156	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	31	-	nC
Q_{GD}	gate-drain charge		-	44	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8250	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	620	-	рF
C_{rss}	reverse transfer capacitance		-	300	-	рF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.25 \Omega; V_{GS} = 10 \text{ V};$	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}; I_D = 12 A$	-	59	-	ns
t _{d(off)}	turn-off delay time		-	120	-	ns
t _f	fall time		-	43	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13	-	8.0	1.2	V

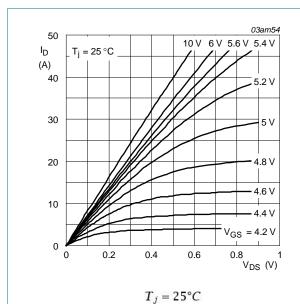


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

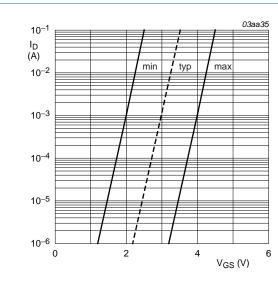
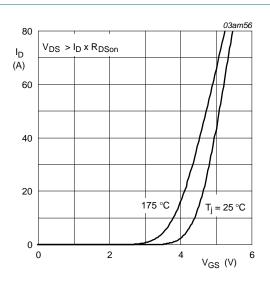


Fig 7. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$



 $T_j = 25$ °C and 175°C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

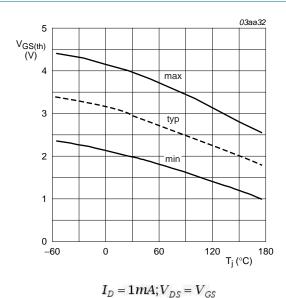


Fig 8. Gate-source threshold voltage as a function of junction temperature

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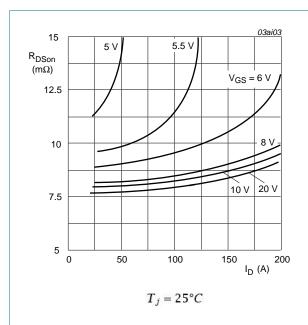


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

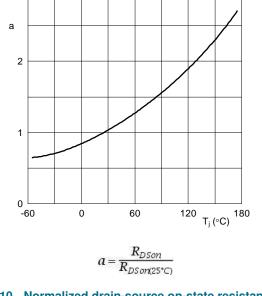


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

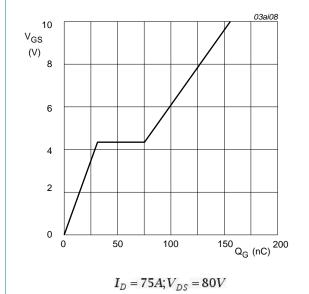
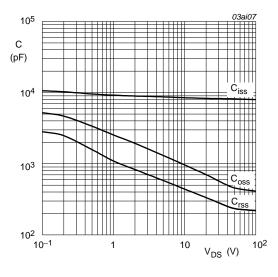


Fig 11. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

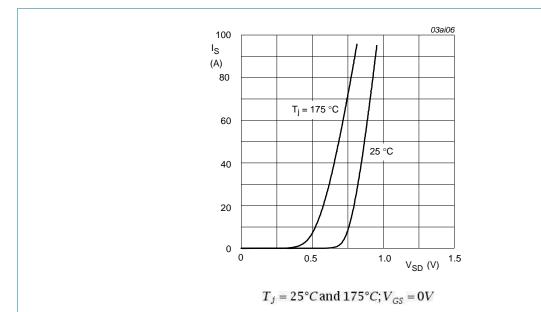
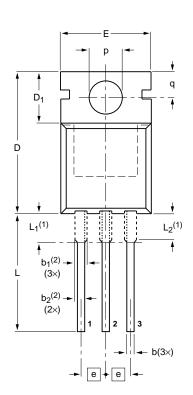


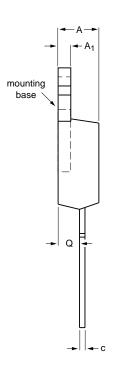
Fig 13. Source current as a function of source-drain voltage; typical values

SOT78

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNI	ГА	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q	
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 14. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN009-100P v.4	20111227	Product data sheet	-	PSMN009-100P v.3		
Modifications: • Various changes to content.						
PSMN009-100P v.3	20111121	Product data sheet	-	PSMN009-100P v.2		

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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